

Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

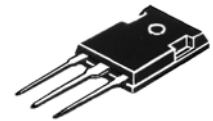
Features

- * Low Forward Voltage.
- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- * 150°C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory
- * Flammability Classification 94V-O
- * *Pb free*
- * *In compliance with EU RoHs directives*

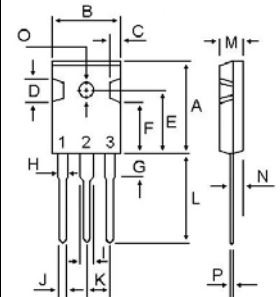


SCHOTTKY BARRIER RECTIFIERS

**40 AMPERES
150 VOLTS**



TO-3P



DIM	MILLIMETERS	
	MIN	MAX
A	20.80	21.80
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	3.75	4.35
H	1.90	2.30
I	2.90	3.30
J	1.00	1.40
K	5.26	5.66
L	19.50	20.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.48	0.72

MAXIMUM RATINGS

Characteristic	Symbol	S40D150C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	150	V
RMS Reverse Voltage	$V_{R(RMS)}$	105	V
Average Rectifier Forward Current (per diode) Total Device (Rated V_R , $T_C=100^\circ\text{C}$)	$I_{F(AV)}$	20 40	A
Peak Repetitive Forward Current (Rate V_R , Square Wave, 20kHz)	I_{FM}	40	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase, 60Hz)	I_{FSM}	300	A
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	°C

THERMAL RESISTANCES

Typical Thermal Resistance junction to case	$R_{\theta jc}$	4.0	°C/w
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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage ($I_F=20$ Amp $T_C=25^\circ\text{C}$) ($I_F=20$ Amp $T_C=125^\circ\text{C}$)	V_F	---	0.83 0.68	0.90 ---	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C=25^\circ\text{C}$) (Rated DC Voltage, $T_C=125^\circ\text{C}$)	I_R	---	0.06 0.3	1 ---	mA

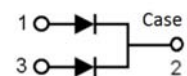


FIG-1 FORWARD CURRENT DERATING CURVE

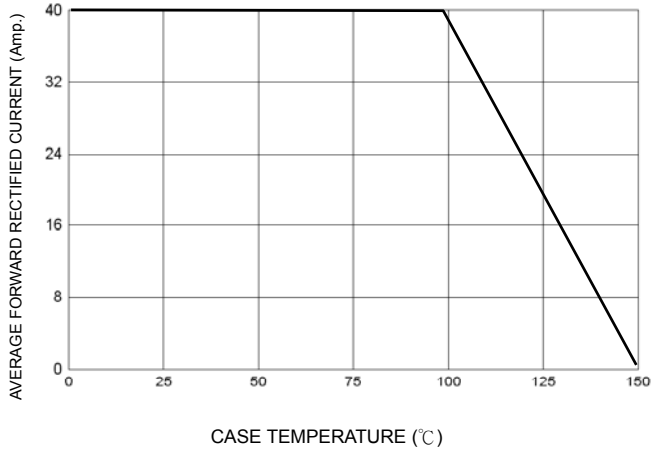


FIG-2 TYPICAL FORWARD CHARACTERISTICS

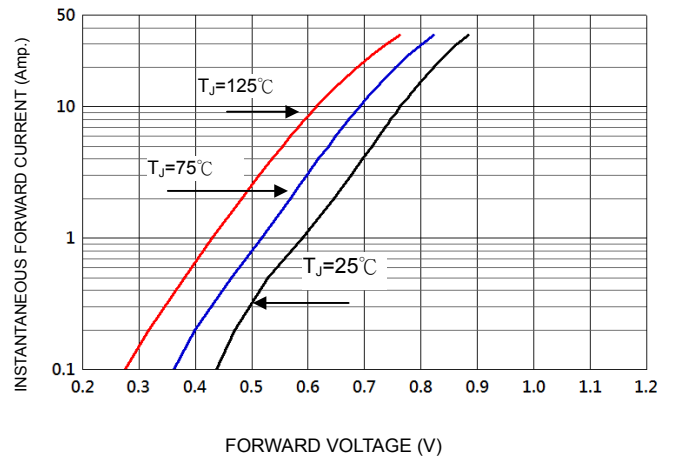


FIG-3 TYPICAL REVERSE CHARACTERISTICS

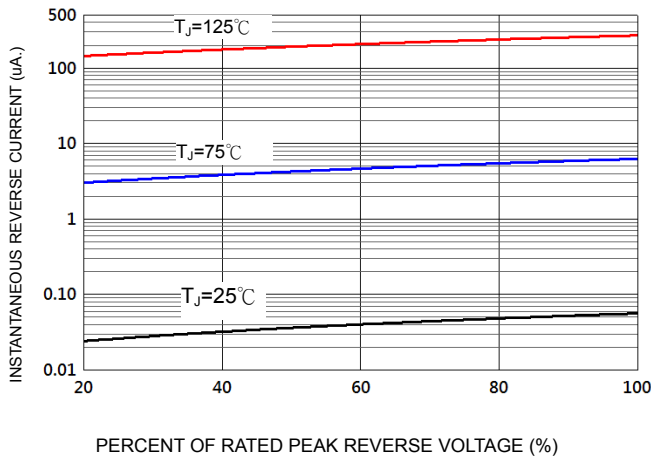


FIG-4 TYPICAL JUNCTION CAPACITANCE

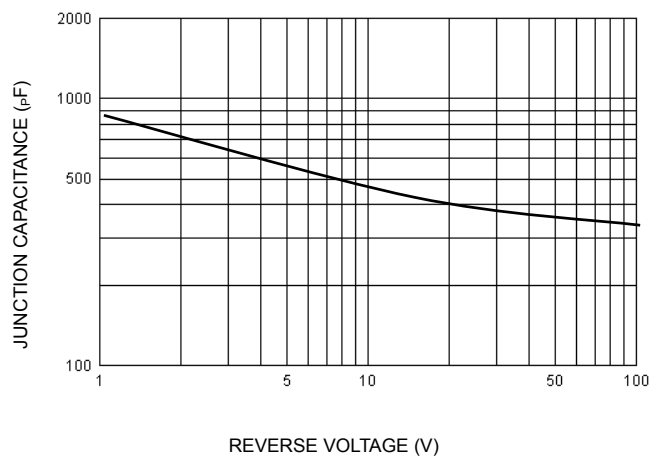
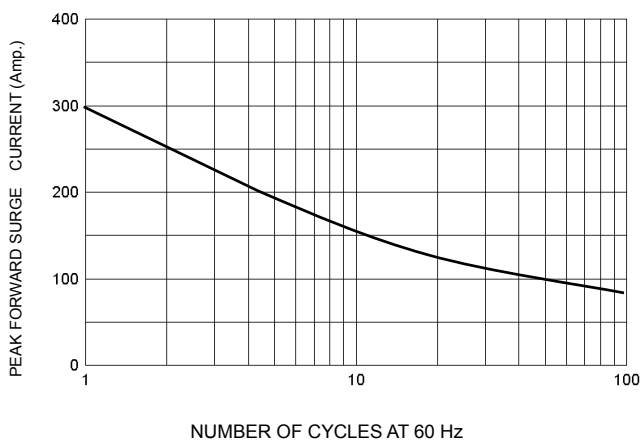


FIG-5 PEAK FORWARD SURGE CURRENT



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